

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

1. (Previously Presented) A semiconductor integrated circuit device comprising:
a resonant circuit resonating at an arbitrary frequency;
a transmission line for transmitting a high-frequency signal having the frequency,
wherein a first end of said transmission line is connected to said resonant circuit;
an active element having a first electrode connected to a second end of said
transmission line, a second electrode which is grounded through a reactance element, and
a third electrode;
an output-matching circuit including a diode section for regulating an oscillation
power and a high-frequency signal output terminal, wherein a first end of said diode
section is connected to said third electrode of said active element, and said high-
frequency signal output terminal is connected to a second end of said diode section; and
a substrate having a main surface on which said resonant circuit, said transmission
line, said active element, and said output-matching circuit are arranged.

2. (Previously Presented) The semiconductor integrated circuit device according
to claim 1, wherein said diode section includes a plurality of diodes connected in an
inverse parallel arrangement.

3. (Withdrawn) The semiconductor integrated circuit device according to claim 1,
wherein said diode section includes a plurality of diodes connected in series.

4. (Withdrawn) The semiconductor integrated circuit device according to claim 1,
further comprising a bias circuit for applying a DC bias to said diode section.

Claims 5-8 (Cancelled).